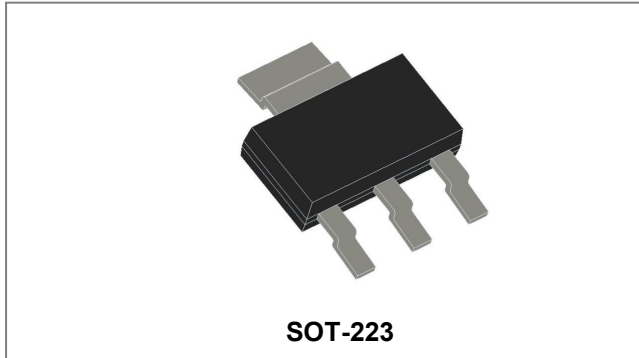


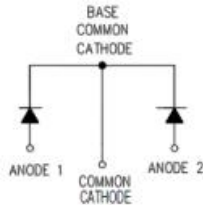
## 20CJQ060 SCHOTTKY RECTIFIER



### Features

- 150 °C T<sub>J</sub> operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Applications

- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	-	60	V
Working Peak Reverse Voltage	V <sub>RWM</sub>			
DC Blocking Voltage	V <sub>R</sub>			
Average Rectified Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>c</sub> =127°C, rectangular wave form	1(Per Leg)	A
			2(Per Device)	
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>C</sub> = 25 °C	26	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (Per Leg)*	V <sub>F1</sub>	@ 1A, Pulse, T <sub>J</sub> = 25 °C	0.55	0.70	V
	V <sub>F2</sub>	@ 1A, Pulse, T <sub>J</sub> = 125 °C	0.48	0.65	V
Reverse Current (Per Leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25 °C	0.02	0.1	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 125 °C	5	10.0	mA
Junction Capacitance(Per Leg)	C <sub>T</sub>	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz	45	60	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

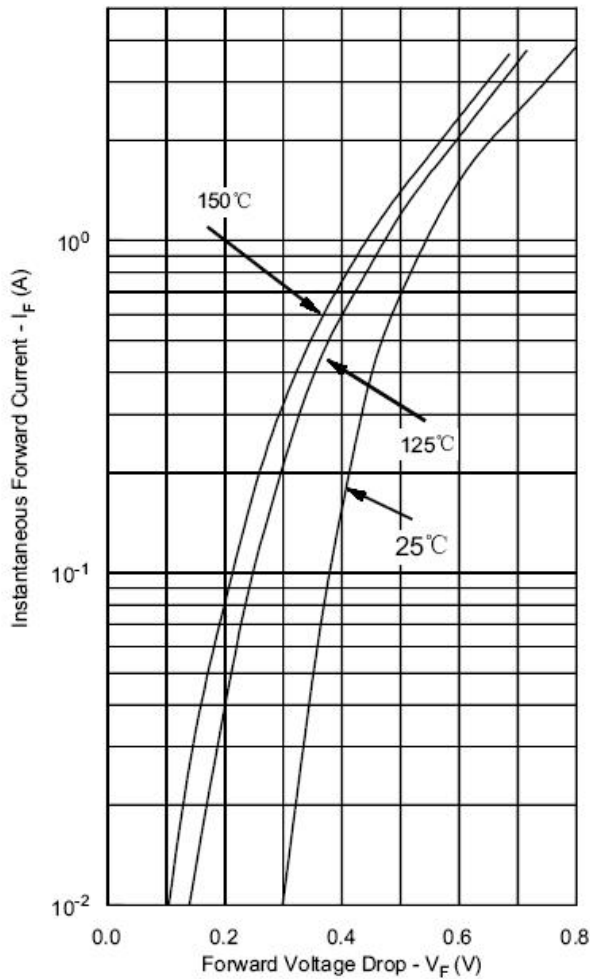
\* Pulse width < 300 μs, duty cycle < 2%

**Thermal-Mechanical Specifications:**

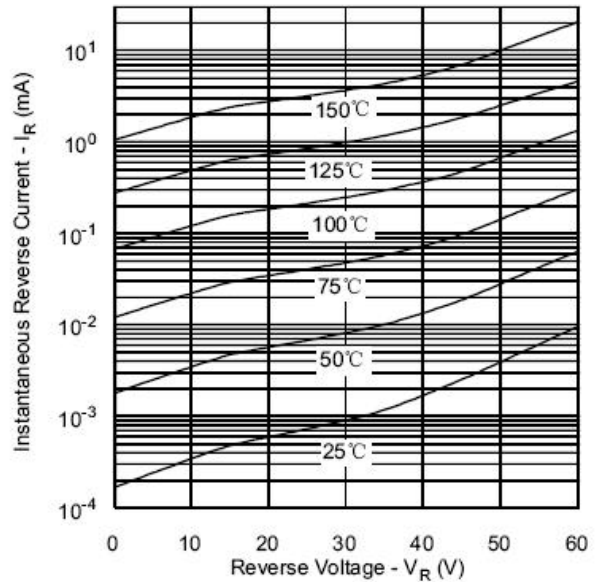
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{stg}}$	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Lead	$R_{\theta JL}$	DC operation	25	$^{\circ}\text{C/W}$
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	DC operation	65	$^{\circ}\text{C/W}$
Approximate Weight	wt	-	0.13	g
Case Style	SOT-223			

**Ratings and Characteristics Curves**

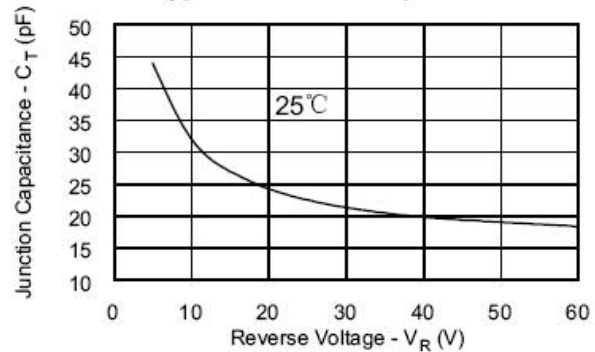
Typical Forward Characteristics



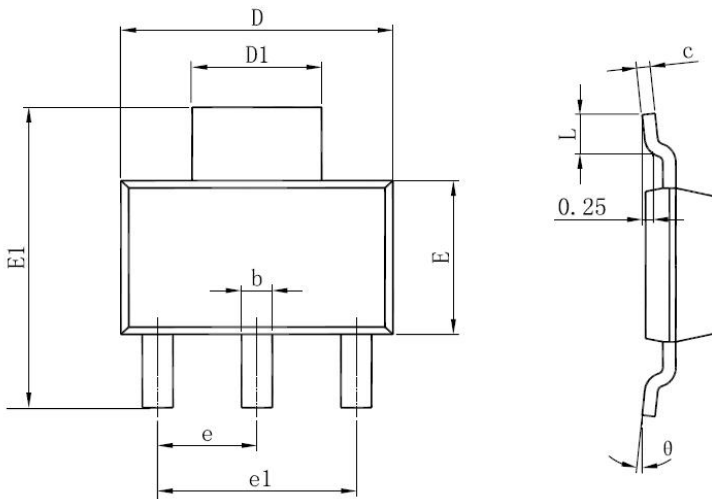
Typical Reverse Characteristics



Typical Junction Capacitance



**Mechanical Dimensions SOT-223**



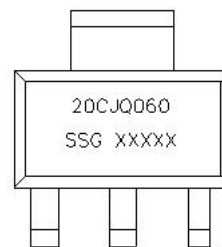
SYMBOL	Millimeters		Inches	
	MIN.	MAX.	MIN.	MAX.
A	1.520	1.800	0.060	0.071
A1	0.000	0.100	0.000	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.820	0.026	0.032
c	0.250	0.350	0.010	0.014
D	6.200	6.400	0.244	0.252
D1	2.900	3.100	0.114	0.122
E	3.300	3.700	0.130	0.146
E1	6.830	7.070	0.269	0.278
e	2.300(BSC)		0.091(BSC)	
e1	4.500	4.700	0.177	0.185
L	0.900	1.150	0.035	0.045
θ	0°	10°	0°	10°

**Ordering Information**

Device	Package	Shipping
20CJQ060	SOT-223 (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

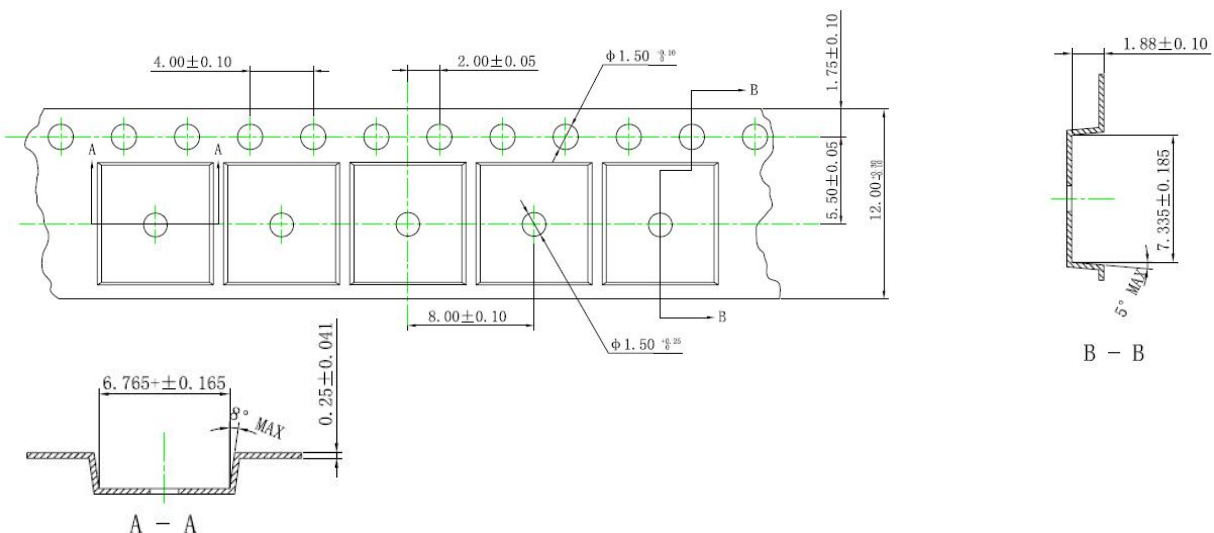
**Marking Diagram**



Where XXXXX is YYWWL

20CJQ060 = Part Name  
SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number

**Carrier Tape Specification SOT-223**



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